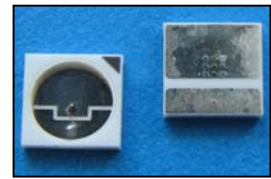




LED36-SMD5R



TECHNICAL DATA

Mid-Infrared Light Emitting Diode, SMD

Light Emitting Diodes with central wavelength 3.65 μm series are based on heterostructures grown on InAs substrates by MOCVD. InAsSb is used in the active layer. Wide band gap solid solutions InAsSbP with P content 50% are used for good electron confinement. LED36-SMD5R has a stable output power and a lifetime more than 80000 hours.

Features

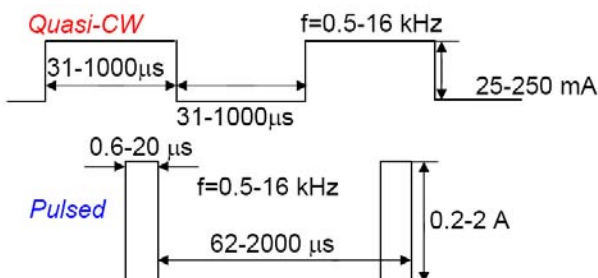
- Structure: InAsSb/InAsSbP
- Peak Wavelength: typ. 3.65 μm
- Optical Output Power: typ. 30 μW qCW
- Package: SMD 5x5 mm with microreflector



Specifications

Item	Condition	Rating			Unit
		Min.	Typ.	Max.	
Peak Wavelength	T=300 K	3.60	3.65	3.70	μm
FWHM	150 mA CW	0.40	0.50	0.60	μm
Quasi-CW Optical Power	200 mA qCW	20	30	40	μW
Pulsed Optical Power	1 A	180	200	220	μW
Switching Time	T=300 K	10	20	30	ns
Operation Voltage	200 mA qCW				V
Operating Temperature		-240 ... +50			$^{\circ}\text{C}$
Emitting Area		300x300			μm
Soldering Temperature		180			$^{\circ}\text{C}$
Package	SMD type package 5x5 mm based on high thermal conductivity ceramics with microreflector				

Operating Regime



Quasi-CW

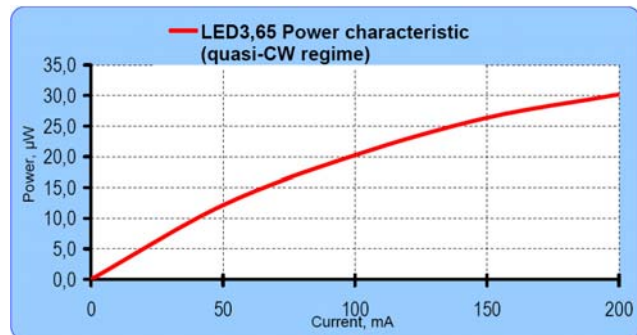
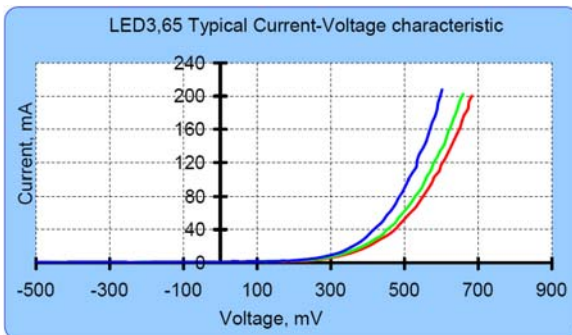
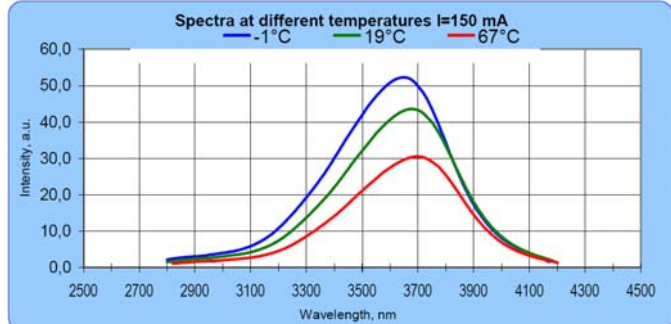
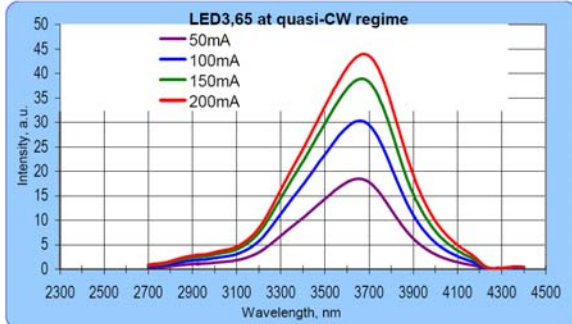
- Maximum current 220 mA
- Recommended current 150-200mA

Pulsed

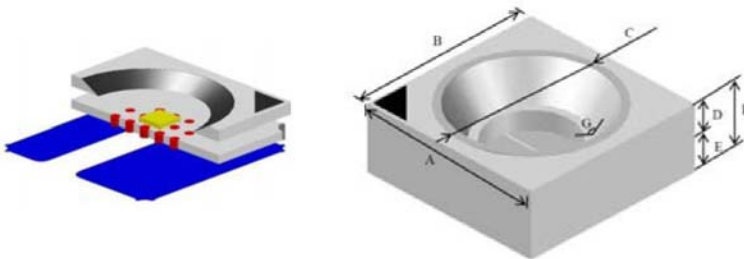
- Maximum current 1 A (puls length 500 ns, repetition rate 2kHz)



Typical Performance Curves



Package



ITEM	Symbol	Rule
Basic Outline	A	5.0± 0.1mm
Basic Outline	B	5.0± 0.1mm
Cavity size	C	Max 4.2Φ
Top layer	D	Min 0.4mm
Bottom layer	E	Min 0.4mm
Thickness	F	Max 2mm
Angle	G	Customize

- Tiny package for surface mounting
- Anode and cathode are led to the metalized areas on the back side of the ceramic surface
- Material – Low Temperature Co-fired Ceramic (LTCC):
 - thermal conductivity 25 W/mK
 - thermoresistance 8 °C/W
- Microreflector provides the reduction of radiation divergence